

C106D		
	单向可控硅 THYRISTOR	版本号 201603-A

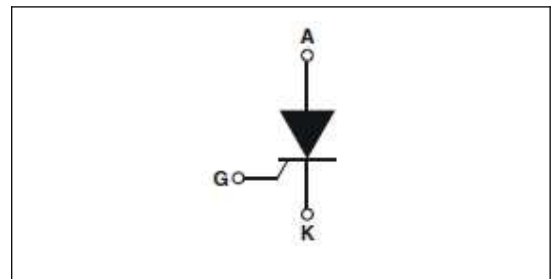
产品概述 GENERAL DESCRIPTION

C106D 单向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，dv/dt高，可靠性高，适用于控温、调光、马达控制。

C106D Thyristor is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

主要参数 MAIN CHARACTERISTICS

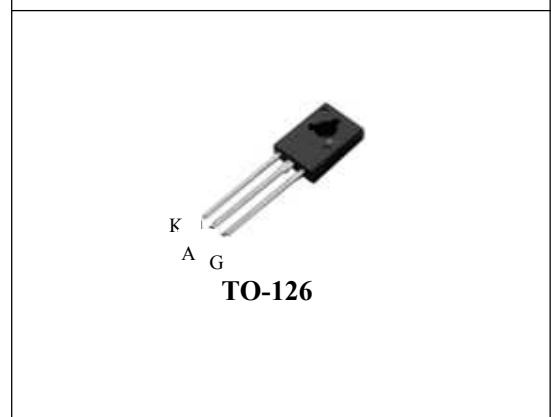
参数 Parameter	数值 Value	单位 Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	600&800	V
I_{GT}	200	μA



产品特性

FEATURES

- | | |
|---|---|
| <ul style="list-style-type: none"> ● dv/dt高 ● 通态压降低 ● Rohs环保产品 | <ul style="list-style-type: none"> ● Highly dv/dt ● Low on-state voltage ● Rohs Products |
|---|---|



应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.

极限值(除非另有规定, Tj=25°C) ABSOLUTE RATINGS

(Tj=25°C, unless otherwise specified)

符号 Symbol	参数 Parameter		数值 Value	单位 Unit
I _{T(RMS)}	RMS 通态电流 RMS on-state current (full sine wave)	T _{lead} ≤51°C	4	A
I _{TSM}	通态峰值浪涌电流 Non repetitive surge peak on-state current	F=50Hz, t=20ms	30	A
I ² t	I ² t 耗散值 I ² t value for fusing	T _p =10ms	6	A ² s
di/dt	通态电流上升值 Critical rate of rise of on-state current	F=120Hz, Tj=125°C	50	A/μs
I _{GM}	门极峰值电流 Peak gate current	TP=20μs, Tj=125°C	1.0	A
P _{G(AV)}	平均门极耗散功率 Average gate power dissipation	Tj=125°C	0.3	W
Tstg	贮存结温范围 Storage junction temperature range		-40+150	°C
Tj	工作结温范围 Operating junction temperature range		-40+125	°C

电参数(除非另有规定, Tj=25°C) ELECTRICAL CHARACTERISTICS

(Tj=25°C, unless otherwise specified)

参数 Parameter	符号 Symbol	规范值 Value		单位 Unit	测试条件 Test Conditions
		min	max		
触发电流 Gate trigger current	I _{GT}	5	200	μA	V _D =6V, I _T =0.01A
触发电压 Gate trigger voltage	V _{GT}	1.0		V	V _D =7V, I _T =0.01A
维持电流 Holding current	I _H	5		mA	V _D =7V, I _T =0.01A
擎住电流 Latching current	I _L	8		mA	V _D =7V, I _T =0.01A
电压上升率 Rise of off-state voltage	dv/dt	10	15	V/μS	V _D =67%V _{DRM}
通态压降 Peak on-state voltage	V _{TM}	1.6		V	I _T =5A
断态漏电流 Peak repetitive forward blocking current	I _{DRM}	10		μA	V _{RRM} =V _{DRM} , Tj = 25°C
	I _{RRM}	0.5		mA	V _{RRM} =V _{DRM} , Tj = 125°C

热特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
Rth(j-c)	Junction to case(AC)	4.1	K/W
Rth(j-a)	Junction to ambient	100	K/W

特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与RMS通态电流关系

Fig.1.Maximum Power Dissipation Versus on-state current

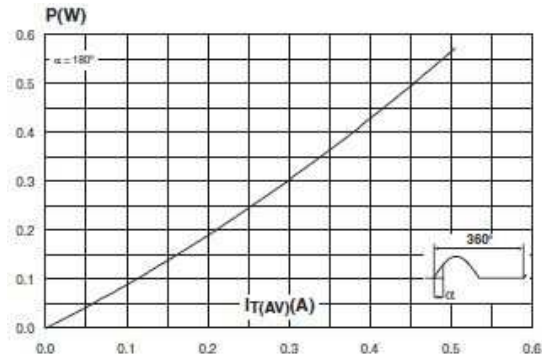


图3 通态特性

Fig.3.On-State Characteristics

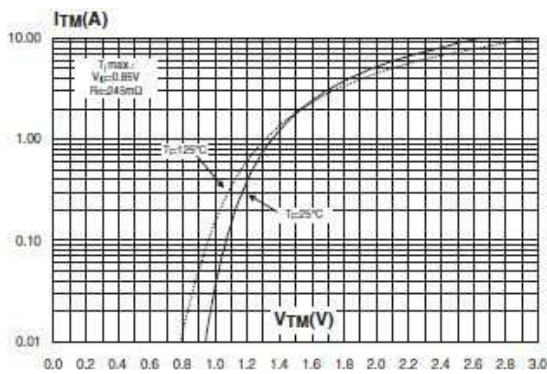


图5 I_{GT} 、 I_H 、 I_L 相对值（相对于25°C）与结温关系

Fig.5.Relative Variation Of Gate Trigger Current, Holding Current And Latching Current Versus Junction Temperature (Typical Value)

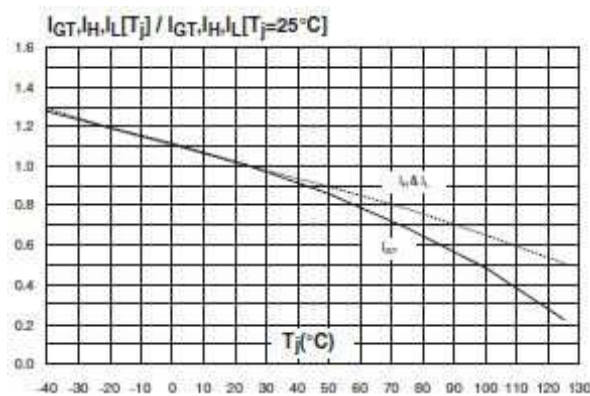


图2 平均通态电流与Tc温度关系

Fig.2. $I_{T(AV)}$ On-state Current Versus TL

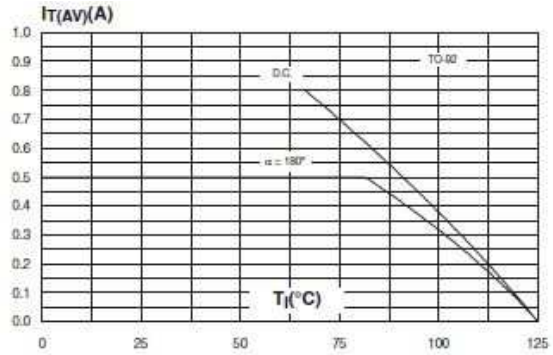
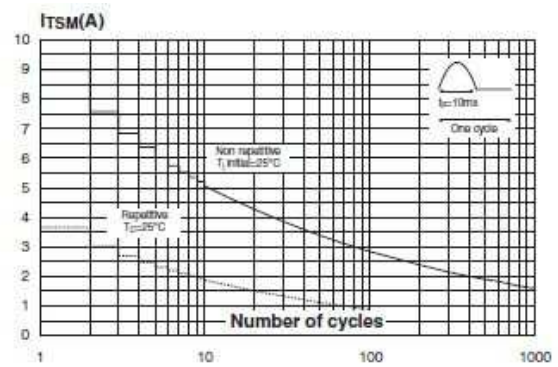


图4 通态浪涌峰值电流与周期数关系

Fig.4.Surge Peak On-state Current Versus Number Cycles



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